

10/728,706

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	6	TiN/Ti and @ad<"20021224" and ((aluminum al) same (copper cu)) and photoresist and (polyethylene PE)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 10:44
L2	0	((polyethylene near10 thick\$4) same photoresist) and @ad<"20021224" and (metal near3 (line layer pattern)) and TiN/Ti	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 10:46
L3	108	((polyethylene near10 thick\$4) same photoresist) and @ad<"20021224"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 11:17
L4	0	3 and TiN/Ti	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 10:46
L5	344640	3 (metal near3 (line layer pattern))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 10:47
L6	27	3 and (metal near3 (line layer pattern))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 10:47
L7	0	((polyethylene adj oxide) near10 thick\$4) same photoresist) and @ad<"20021224"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 11:17
L8	1	((polyethylene adj oxide) near10 thick\$4) and photoresist and @ad<"20021224"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 11:18
L9	51	((polyethylene adj oxide) same thick\$4) and photoresist and @ad<"20021224"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 12:31
L10	775	((boron adj chloride) (boron adj trichloride)) same etch\$4) and @ad<"20021224"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 12:54

L11	11	10 and TiN/Ti	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 12:32
L12	2	("6690084").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/11 12:55
L13	0	12 and ((boron adj chloride) (boron adj trichloride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 12:55
L14	0	12 and BCl3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/11 12:55
S1	8	((("6316329") or ("6184148") or ("6006764") or ("5935762"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/11 09:48
S2	1	S1 and TiN/Ti	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 17:33
S3	0	(TiN/Ti near4 cap\$4) and Al/Cu and (TiN/Ti near4 barrier) and @ad<"20021224" and (metal adj (line layer pattern)) and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 17:35
S4	0	(TiN/Ti same cap\$4) and Al/Cu and (TiN/Ti same barrier) and @ad<"20021224" and (metal adj (line layer pattern)) and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 17:35
S5	0	(TiN/Ti same cap\$4) and Al/Cu and (TiN/Ti same barrier) and @ad<"20021224" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 17:36
S6	3	Al/Cu and TiN/Ti and @ad<"20021224" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 17:57

S7	1593	(Al/Cu (aluminum and copper)) and @ad<"20021224" and photoresist and buffer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 18:03
S8	106	S7 and (ILD (interlayer adj dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 17:59
S9	218	(Al/Cu (aluminum and copper)) and @ad<"20021224" and (buffer same photoresist)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 18:04
S10	138	S9 and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 18:05
S11	136	S10 and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 18:05
S12	136	S10 and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 18:10
S13	332	(metal adj line) and @ad<"20021224" and (insulation dielectric) and photoresist and buffer and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 18:12
S14	80	(metal adj line) and @ad<"20021224" and (insulation dielectric) and (photoresist same buffer) and etch\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 18:12